

GaAs photonic crystal nanocavity with ultrahigh-Q : toward microwatt nonlinearity at 1.55 μm

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We have realized and measured a GaAs nanocavity in a slab photonic crystal based on the design by Kuramochi et al. [Appl. Phys.Lett., **88**, 041112, (2006)]. Thanks to calibration by an external Fabry-Perot interferometer, we measure a quality factor $Q > 700,000$ at 1510 nm. This shows that, for ultra-high Q nanocavities, GaAs is as suitable a material as silicon. Furthermore, the larger two-photon absorption (TPA) of GaAs, combined with thermo-optics scaling laws, indicates that microwatt-level nonlinearities are feasible and will be more functional in gallium arsenide than in silicon nanocavities.

The achievement of quality factors of $Q \approx 10^6$ in micron-sized nanocavities carved in two-dimensional photonic crystals opens perspectives for linear and nonlinear optical signal processing. In this Letter, we show that GaAs can reach Q values similar to those of silicon, namely $Q > 700,000$, at telecom wavelength $\lambda = 1.5 \mu\text{m}$. Microwatt-level nonlinear operation can therefore be envisioned from the $\approx 5 \text{ W}$ threshold power value obtained in our previous results ([4, 6]) for the lower quality factor $Q \approx 246,000$. With the linear bandwidth set at $\approx 1 \text{ GHz}$ by the cavity, nonlinear processing of microwatt optical signal in the 1 MHz - 1 GHz window can be achieved. From the scaling laws of the various effects (Kerr, free carrier plasma, TPA, thermo-optic), we pinpoint the more favorable capabilities of GaAs in this respect.

Nanocavities with $Q > 10^6$ have been obtained by NTT and Kyoto's teams [1, 2] based on refinements of the basic heterostructure waveguide design of [3]. We have used here Kuramochi's design as pictured in Fig.1(a). We used the same GaAs membrane technology as in Ref.([4]), with a 186-nm-thick suspended GaAs membrane and a basic lattice pitch $a = 420 \text{ nm}$. The access waveguide is designed as W1.07, and the waveguide supporting the cavity is W0.98 (W1 refers to the single missing row waveguide along the ΓK direction of the photonic crystal). The hole shifts defining the cavity are 9 nm, 6 nm and 3 nm, arranged as indicated. The waveguide-cavity separation is 8 rows.

Fabrication-wise, we used a compact and efficient 100kV e-beam writer nB3 (NanoBeam Ltd., Cambridge, UK) to define the patterns in the top resist layer, the rest being unchanged. The good results obtained validate the qualities of this tool. Inductively-Coupled Reactive-Ion-Etching [5] was used to perform GaAs/GaInP vertical etching. As for measurements, we used a tunable laser source (Tunics from Nettest). We discarded its scanning uncertainties by diverting part of its flux to a

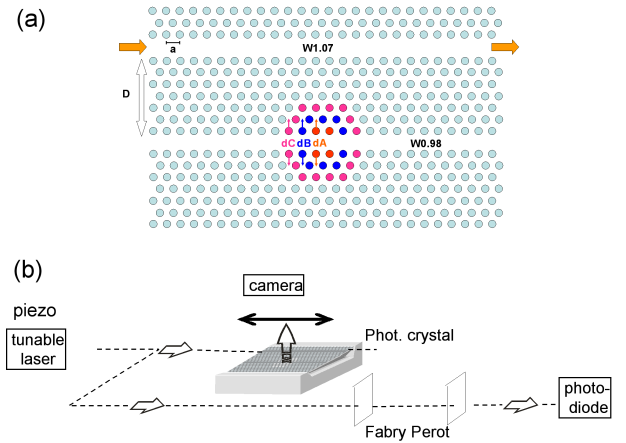


FIG. 1: (a) Schematic description of the GaAs side-coupled cavity system; (b) Experimental setup.

home-built low-finesse Fabry-Perot (FP) interferometer with 28.6-cm-spaced mirrors. This gives a 524 MHz free-spectral range (FSR). We swept the laser over a dozen FSR, monitoring the tuning through FP fringes. As in [6], the top collection $A(\lambda)$ provides a peak at resonance, while the transmitted waveguide signal $T(\lambda)$ displays a corresponding dip (not shown) whose depth is indicative of coupling conditions. Here, a largely subcritical coupling was observed ($\Delta T/T < 10\%$), in line with the 8 rows guide-cavity spacing. The vertical collection revealed a total quality factor $Q_{tot} = 735,000$ shown in Fig.2 ($\Delta\nu = 272 \text{ MHz}$, $\Delta\lambda = 2.05 \text{ pm}$), with a Lorentzian fit. A consistent Q value was measured on $T(\lambda)$. The power used for these measurements is very low, 100 nW, eased by the use of an InGaAs focal plane array (from Xenics) for $A(\lambda)$.

The important point at this stage is that the best nanocavities, with $Q \approx 10^6$ are feasible with GaAs membranes, and a technological effort no larger than that done for silicon, provided that good epitaxial GaAs/GaInP/GaAs is available, yielding in particular

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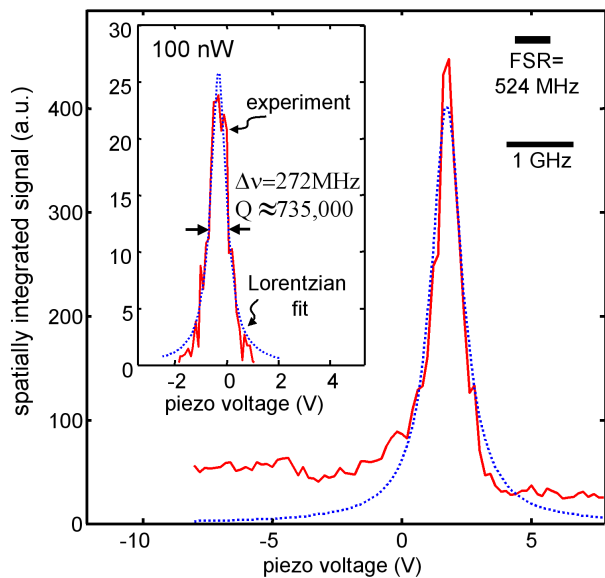


FIG. 2: Vertical resonance emission spectrum of a typical nanocavity (solid line) with ≈ 500 MHz linewidth and the best case $Q > 700,000$ in the inset. Dashed lines are Lorentzian fits.

gently strained membranes. A Q scaling from our previous work [4] indicates that at these Q 's, we enter in a nonlinear regime at the microwatt level in terms of power flow in the waveguide. But, as underlined by this work and previous ones [7, 8], both thermal and electronic nonlinearities are involved: Kerr effect, two photon absorption (TPA), free-carrier plasma effect, and thermo-optic shift due to the energy deposited by the electronic processes.

For thermo-optic effects, at first sight, silicon is a better heat conductor, thus minimizing thermo-optic drifts detrimental to deterministic signal processing. These drifts are random for generic time-variable signals, with long "silent" or "loud" periods leading to, e.g., $1/f$ spectral density. We show below that this appearance is largely offset by the intrinsic lower operation point of GaAs, giving to this latter material a clear niche for ultra-low power optical manipulations. This regime could be of interest for radar applications, where truly analog signals with small (Doppler induced) bandwidth are manipulated. Extension to 10 GHz (telecom-type) operation far exceeds the intrinsic bandwidth. However, thinking of so-called CROW type waveguide built from multiple identical cavities [12], a flat 10 GHz band requires a large coupling of cavities with a very high Q such as the present one. Therefore, with a canonical volume scaling of the threshold power levels involved, the arguments for a single-cavity in the 1 GHz regime shall essentially hold for 10 GHz operation.

Let us detail how the nonlinear operation can be performed to further evaluate GaAs vs. Si.

Firstly, in transient operation, the thermo-optic effect has a time-dependent spatial extent x , given by the ther-

TABLE I: Physical parameters [10].

Parameter	Symbol	GaAs	Si
TPA coefficient (cm/GW)	β	10.2	0.45
Carrier lifetime (ps)	τ_N	10.0 [11]	100 [8]
Thermal diffusivity (m^2/s)	C_p	0.31	0.78
Kerr coefficient (cm^2/W)	n_2	$160 \cdot 10^{-15}$	$45 \cdot 10^{-15}$
Thermo-optic index (1/K)	n_T	$2.5 \cdot 10^{-4}$	$1.7 \cdot 10^{-4}$

mal diffusivity C_p , obeying a fundamental $x \approx (C_p \tau)^{1/2}$ scaling in either two or three dimensions. Since Si and GaAs result in almost the same cavity layout, no geometrical difference offsets the behaviour in the cavity region: they rank like the relative values of bulk materials (see Table I). Thermal spot sizes of at most $9 \mu m^2$ (GaAs) and $5.5 \mu m^2$ (Si) are found at $\tau = 1 \mu s$. For the MHz-GHz range, the TPA power deposited in the nanocavity will thus still reside in its photonic vicinity, not even spreading beyond one PhC lattice pitch for the top faster range. This implies the virtual impossibility to implement an extra thermal sink at these high Q /low nonlinear threshold values. Such a sink would be so close to the cavity core that the high Q would be spoiled. This is at variance with the single-PhC-cell nanocavity lasers [9] where Q can be spoiled provided material gain is large enough.

Secondly, the basic TPA damping threshold in terms of cavity radiated power P_{rad} can be calculated as (using notations of [4]):

$$P_{rad}^{th} = \frac{4\pi^2 n^2 V_{TPA}}{\lambda^2 Q_{in} Q_{tot} \beta} \propto \frac{1}{\beta} \quad (1)$$

This amounts to typically $1 \mu W$ for a mean quality factor $\sqrt{Q_{in} Q_{tot}} \approx 5 \cdot 10^5$, of the order reached here (Q_{in} is the intrinsic quality factor). $1 \mu W$ would also be the waveguide flux at critical coupling.

Thirdly, the impact of thermo-optic effects derives from the index shift Δn . This latter scales like $n_T R \beta |a|^4$ (R is the thermal resistance) and therefore like $n_T C_p / \beta$ when (1) is used with $|a|^2 = P_{rad} Q_{in} / \omega$. This is a key point: obviously, a stronger TPA coefficient and a lower power threshold weakens the thermal burden. Of particular interest here is the fact that the ≈ 3 times stronger $n_T C_p$ product of silicon is well offset by the > 10 times larger TPA coefficient β of GaAs, providing a definite advantage for nonlinear operation with much less penalty from $1/f$ -signal-spectrum induced thermo-optic drift.

Fourthly, carriers build-up and their plasma cause in turn an extra index shift (and negligible absorption). This effect builds up at the time scale of the carrier recombination time τ_{rec} . It can be considered to be fast since we focus on the 10-100 ps time scale here (Table I). It is interesting, then, to compare the power for the crossover of the index change it causes, proportional to $|a|^4$, with the sole Kerr index change, $\propto |a|^2$. This $|a|^4$

vs. $|a|^2$ crossover is found at :

$$|a|_{th}^2 \approx \frac{n_2 m^*}{\beta \tau_{rec}} \quad (2)$$

From the intrinsic parameters of Si and GaAs (Table I), the crossover power obeys a scaling law : $|a|_{th,Si}^2 / |a|_{th,GaAs}^2 \approx 15 \times \tau_{rec,GaAs} / \tau_{rec,Si}$. The prefactor (15) turns out to be well offset in actual experiments : 100 ps is a common value for Si, whereas 10 ps was found in [11], resulting in similar crossover powers. Usually, Kerr effect is sought for optical manipulation and TPA seen as an hindrance. Taking an opposite approach, i.e. exploiting nonlinear cavity damping, it becomes advantageous to use GaAs : as it operates at a much lower power, it features less index shift from the Kerr effect than silicon. A roughly similar issue arises if we try to directly find the "nonthermal" offsets of the real and imaginary part of the cavity frequency, whose ratio, with usual assumptions is given by:

$$\frac{Im(\Delta\omega)}{Re(\Delta\omega)} \approx \frac{\beta c}{2n_2\omega} \quad (3)$$

It evidences the classical control parameter of nonlinear optics, $\beta\lambda/n_2$. The ratio is about four times larger for GaAs (0.76) than for Si (0.21). This supports the use of GaAs-based cavities in the nonlinear damping regime. However, it might be questioned whether larger ratio (Eq.(3)) can be attained, notably above unity. Two approaches are possible in the GaAs family : (i) bandgap engineering, to optimize β (or to decrease it if need be);

(ii) by a careful engineering of τ_{rec} and carrier density. Since one necessarily operates nonlinear devices around a given threshold level, the two nonthermal real index shifts (Kerr and carrier-plasma-induced) could be made to compensate each other around a desired range. This amounts to adjust the crossover threshold seen above to coincide with the TPA threshold. At this stage, much more details would be needed to describe the phenomena on a proper bandwidth: this desirable compensation is not instantaneous due to the carrier build-up time. So the dynamical behaviour largely depends on the exact regime chosen and more analysis is needed to validate the range of possible nonlinear operation of a GaAs nanocavity in the microwatt regime, notably to push it into the GHz regime.

In conclusion, we showed that an ultra-high Q nanocavity akin to those elaborated in silicon is also feasible in GaAs, making GaAs devices with $Q \approx 10^6$ fully plausible. Additionally, we stressed the possibility to operate at the microwatt level for nonlinear operation, through nonlinear damping based on two-photon-absorption. We indicated ways to pursue this regime into the GHz range, and to limit the impact of direct Kerr effect. Importantly, we substantiated the fact that thermal effects inflict less severe penalties when operating nanocavities based on GaAs as compared to those based on Si.

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